Product Overview

**NDT014L: N-Channel Logic Level Enhancement Mode Field Effect Transistor 60V, 2.8A, 160mΩ**

For complete documentation, see the data sheet.

These N-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

**Features**
- 2.8 A, 60 V. RDS(ON) = 0.2 Ω @ VGS = 4.5 V, RDS(ON) = 0.16 Ω @ VGS = 10 V.
- High density cell design for extremely low RDS(ON).
- High power and current handling capability in a widely used surface mount package.

**Applications**
- This product is general usage and suitable for many different applications.

**Part Electrical Specifications**

<table>
<thead>
<tr>
<th>Product</th>
<th>Pricing ($/Unit)</th>
<th>Compliance</th>
<th>Status</th>
<th>Channel PolaritY</th>
<th>Configuration</th>
<th>V_{DSS} Min (V)</th>
<th>V_{DS(on) Max} (V)</th>
<th>I_D Max (A)</th>
<th>P_D Max (W)</th>
<th>R_{DS(on) Max} @ V_{GS} = 2.5 V (mΩ)</th>
<th>R_{DS(on) Max} @ V_{GS} = 4.5 V (mΩ)</th>
<th>R_{DS(on) Max} @ V_{GS} = 10 V (mΩ)</th>
<th>Q_g Typ @ V_{DS} = 4.5 V (nC)</th>
<th>Q_g Typ @ V_{DS} = 10 V (nC)</th>
<th>Ciss Typ (pF)</th>
<th>Package Type</th>
</tr>
</thead>
<tbody>
<tr>
<td>NDT014L</td>
<td>0.228</td>
<td>Pb-free</td>
<td>Active</td>
<td>N-Channel</td>
<td>Single</td>
<td>60</td>
<td>±20</td>
<td>3</td>
<td>115</td>
<td>-</td>
<td>-</td>
<td>-</td>
<td>85</td>
<td>105</td>
<td>SOT-223-4 / TO-261-4</td>
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</tbody>
</table>

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